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**INFORMATION DISCLOSURE STATEMENT PURSUANT TO** 37 C.F.R. §§1.97-1.99

PATENT APPLICATION

Applicant(s): Daniel C. Edelstein et al.

Docket No.: END920030116US1

FOR: HIGH Q FACTOR INTEGRATED CIRCUIT INDUCTOR

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. §1.56 and pursuant to 37 C.F.R. §§1.97-1.99, Applicant(s) hereby notifies the U.S. Patent and Trademark Office of the documents listed on the attached Form PTO-1449. Applicant respectfully submits that all pending claims are patentable over the foregoing references, alone or in combination. The Examiner is requested to initial the enclosed Form PTO-1449 and return a copy thereof to the undersigned.

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicant reserves the right to dispute any of the listed documents as prior art during examination. Further, Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application. Furthermore, the submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other material information may exist. This Information Disclosure Statement is being filed within three months of the filing date of the captioned patent application, and therefore no certification under 37 C.F.R. §1.97(e) or fee under 37 C.F.R. §1.17(p) is required.

Respectfully submitted,

Dated: 12 /02 /2 003

By Jack P. Friedman

Rea. No. 44,688

Enclosures: PTO-1449

## ATTY DOCKET NO. SERIAL NO. END920030116US1 INFORMATION DISCLOSURE CITATION Danicel C. Edelstein et al. (Use several sheets if necessary) FILING **GROUP U.S. PATENT DOCUMENTS** \*EXAMINER FILING DATE DOCUMENT NUMBER NAME CLASS SUBCLASS DATE INITIAL IF APPROPRIATE US2002/0172025 11/2002 Megahed et al. US2003/0067052 4/2003 Matsuo et al. US2002/0197844 12/2002 Johnson et al. 6,551,931 4/2003 Edelstein et al. 3/2003 6,534,374 Johnson et al. 6,457,234 10/2002 Edelstein et al. 9/2002 Hsu et al. 6,444,517 6,368,484 4/2002 Volant et al. 1/2002 6,335,104 Sambucetti et al. 6,333,559 12/2001 Costrini et al. 6,323,128 11/2001 Sambucetti et al. **FOREIGN PATENT DOCUMENTS** TRANSLATION DOCUMENT NUMBER DATE COUNTRY CLASS SUBCLASS YES NO WO03017479A2 2/2003 **PCT** OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Research Disclosure, April 2000, AN ON-CHIP THREE-DIMENSIONAL INDUCTOR BY DAMASCENE PROCESS, pages 682-683. Burghartz et al., MONOLITHIC SPIRAL INDUCTORS FABRICATED USING A VLSI CU-DAMASCENE INTERCONNECT TECHNOLOGY AND LOW-LOSS SUBSTRATES, pages 4.5.1-4.5.4, 1996 IEEE.

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not

considered. Include copy of this form with next communication to applicant.

## INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO. END920030116US1	SERIAL NO.	
Danicel C. Edelstein et al.		
FILING	GROUP	

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DAT	_	
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EXAMINER		41_00-1	DATE CONSIDERED					

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